

## **isc** Silicon NPN Power Transistor

# **BU508FI**

#### **DESCRIPTION**

- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub>= 700V (Min)
- · High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

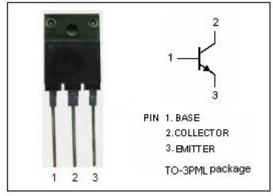
#### **APPLICATIONS**

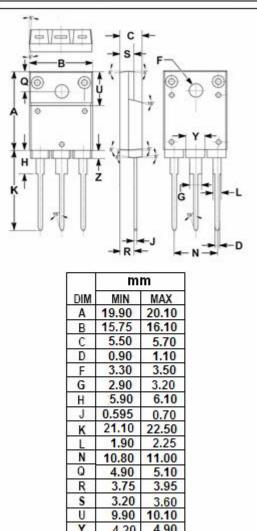
 Designed for use in horizontal deflection circuits of color TV receivers.



SYMBOL	PARAMETER	VALUE	UNIT	
$V_{CBO}$	Collector-Base Voltage	1500	V	
$V_{\sf CEO}$	Collector-Emitter Voltage	700	V	
V <sub>EBO</sub>	Emitter-Base Voltage	8	V	
Ic	Collector Current- Continuous	8	Α	
Ісм	Collector Current-Peak	15	Α	
Pc	Collector Power Dissipation @ Tc=25°C	60	W	
TJ	Junction Temperature 150		$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-65~150	$^{\circ}$	

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	2.08	°C/W







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### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 10mA ; I <sub>B</sub> = 0	700			V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4.5A; I <sub>B</sub> = 2.0A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4.5A; I <sub>B</sub> = 2.0A			1.3	V
І <sub>сво</sub>	Collector Cutoff Current	V <sub>CB</sub> = 1500V;I <sub>E</sub> = 0			1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5.0V ; I <sub>C</sub> = 0			0.1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	6		30	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4.5A; V <sub>CE</sub> = 5V	2.25			
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 0.1MHz		125		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V; f <sub>test</sub> = 1.0MHz		7		MHz
Switching T	imes	1	ı	1	ı	
ts	Storage Time	I <sub>C</sub> = 4.5A; V <sub>CC</sub> = 140V; I <sub>B1</sub> = I <sub>B2</sub> = 2A		7	μ \$	_
t <sub>f</sub>	Fall Time			0.55	μS	_

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